TOSHIBA Photocoupler GaAs IRed & Photo-Triac

TLP3503

Triac Driver
Programmable Controllers
AC-Output Module
Solid State Relay

The TOSHIBA TLP3503 consists of a zero voltage crossing turn—on photo—triac optically coupled to a gallium arsenide infrared emitting diode in a 8 lead plastic DIP package.

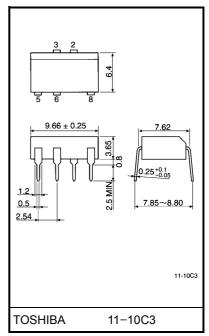
- Peak off-state voltage: 400V (min.)
- Trigger LED current: 10mA (max.)
- On-state current: 0.5A_{rms} (max.)
- Isolation voltage: 2500V_{rms} (min.)
- UL recognized: UL1577, file No. E67349
- Trigger LED Current

| Classi– fication* | Trigger LED Current (mA) | | Marking Of Classification | |
|----------------------|--------------------------------|------|---------------------------|--|
| | V _T = 6V, Ta = 25°C | | | |
| | Min. | Max. | Olassification | |
| (IFT5) | _ | 5.0 | T5 | |
| (IFT7) | ı | 7.0 | T5, T7 | |
| Standard | - | 10 | T5, T7, blank | |

*Ex. (IFT5); TLP3503 (IFT5)

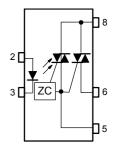
(Note)Application type name for certification test, please use standard product type name, i.e. TLP3503 (IFT5): TLP3503

Unit in mm



Weight: 0.52 g

Pin Configuration (top view)



- 2 : Anode
- 3 : Cathode
- 5 : Triac gate
- 6: Triac T1
- 8 : Triac T2

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Maximum Ratings (Ta = 25°C)

| Characteristic | | | Symbol | Rating | Unit | |
|--|---|----------------------|----------------------|---------|------|--|
| | Forward current | Ι _Ε | 50 | mA | | |
| | Forward current derating (Ta ≥ | ΔI _F / °C | -0.7 | mA / °C | | |
| LED | Peak forward current (100µs pu | I _{FP} | 1 | Α | | |
| | Reverse voltage | V _R | 5 | V | | |
| | Junction temperature | Tj | 125 | °C | | |
| | Off-state output terminal voltage | V_{DRM} | 400 | V | | |
| | On-state RMS current | Ta = 40°C | IT (DMO) | 0.5 | Α | |
| Detector | | Ta = 60°C | I _{T (RMS)} | 0.35 | | |
| | On–state current derating (Ta ≥ | ΔI _T / °C | -7.2 | mA / °C | | |
| | Peak current from snubber circupulse, 120pps) | I _{SP} | 2 | А | | |
| | Peak nonrepetitive surge currer | I _{TSM} | 5 | Α | | |
| | Junction temperature | Tj | 110 | °C | | |
| Storage temperature range | | | T _{stg} | -40~125 | °C | |
| Operating temperature range | | | T _{opr} | -20~80 | °C | |
| Lead soldering temperature (10s) | | | T _{sol} | 260 | °C | |
| Isolation voltage (AC, 1min., R.H. ≤ 60%) (Note) | | | BVS | 2500 | Vrms | |

(Note) Device considered a two terminal: LED side pins shorted together and detector side pins shorted together.

Recommended Operating Conditions

| Characteristic | Symbol | Min. | Тур. | Max. | Unit |
|-----------------------------------|------------------|------|------|------|-----------------|
| Supply voltage | V _{AC} | _ | _ | 120 | V _{ac} |
| Forward current | l _F | 15 | 20 | 25 | mA |
| Peak current from snubber circuit | I _{SP} | _ | _ | 1 | Α |
| Operating temperature | T _{opr} | -20 | _ | 80 | °C |

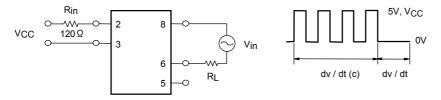
Individual Electrical Characteristics (Ta = 25°C)

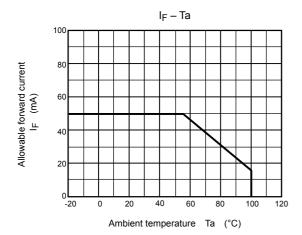
| | Characteristic | Symbol | Test Condition | Min. | Тур. | Max. | Unit |
|----------|--|------------------|--|------|------|------|--------|
| | Forward voltage | V _F | I _F = 10mA | 1.0 | 1.15 | 1.3 | V |
| LED | Reverse current | I _R | V _R = 5 V | _ | _ | 10 | μΑ |
| | Capacitance | C _T | V = 0, f = 1MHz | _ | 30 | _ | pF |
| Detector | Peak off-state current | I _{DRM} | V _{DRM} = 400V, Ta = 110°C | _ | _ | 100 | μA |
| | Peak on-state voltage | V _{TM} | I _{TM} = 0.75A | _ | _ | 3.0 | V |
| | Holding current | lΗ | RL = 100Ω | _ | _ | 25 | mA |
| | Critical rate of rise of off–state voltage | dv / dt | $V_{in} = 120V_{rms}$ (fig.1) | 200 | 500 | _ | V / µs |
| | Critical rate of rise of commutating voltage | dv / dt (c) | $V_{in} = 120V_{rms}, I_T = 0.5A_{rms}$ (fig. 1) | _ | 5 | _ | V / µs |

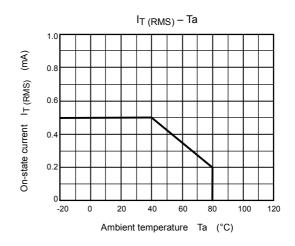
Coupled Electrical Characteristics (Ta = 25°C)

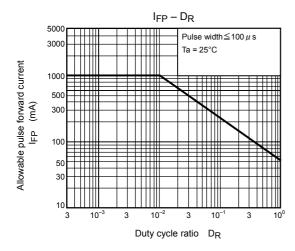
| Characteristic | Symbol | Test Condition | Min. | Тур. | Max. | Unit |
|----------------------------------|-----------------|--|--------------------|------------------|------|------------------|
| Trigger LED current | I _{FT} | V _T =6V | _ | _ | 10 | mA |
| Inhibit voltage | V _{IH} | I _F =Rated I _{FT} | _ | _ | 50 | V |
| Leakage in inhibited state | lіН | I _F =Rated I _{FT} V _T = Rated V _{DRM} | _ | 200 | 1 | μΑ |
| Capacitance (input to output) | C _S | V _S =0, f=1MHz | _ | 0.8 | ١ | pF |
| Isolation resistance | R _S | V _S =500V | 5×10 ¹⁰ | 10 ¹⁴ | _ | Ω |
| | BVS | AC, 1 minute | 2500 | _ | _ | V _{rms} |
| Isolation voltage | | AC, 1 second, in oil | _ | 5000 | _ | |
| | | DC, 1 minute, in oil | _ | 5000 | _ | V _{dc} |

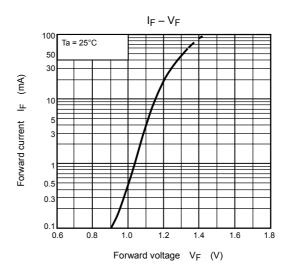
Fig.1: dv / dt test circuit

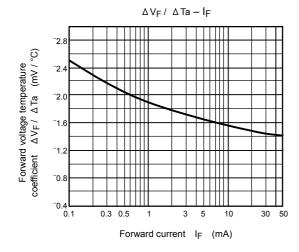


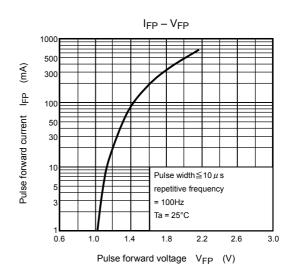


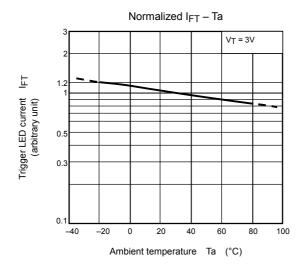


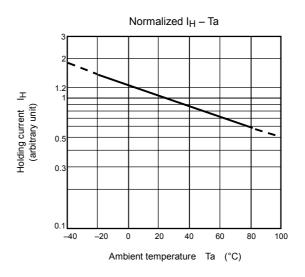


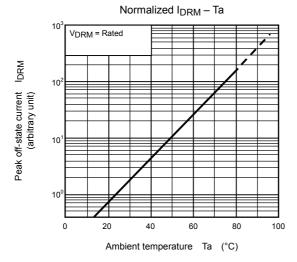


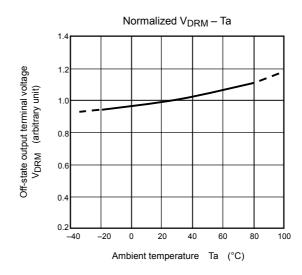


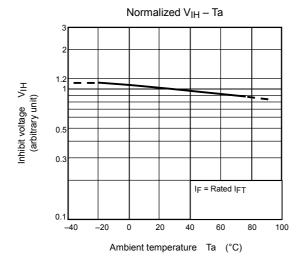


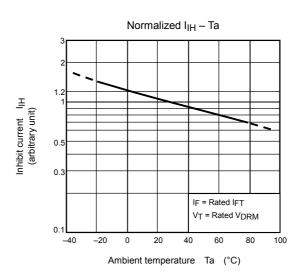












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